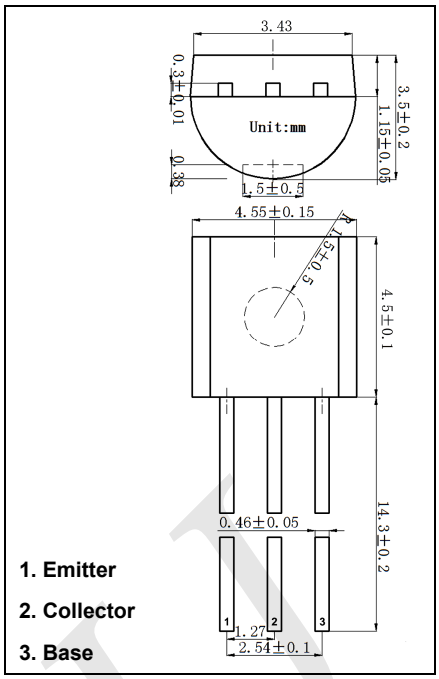
SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

TO-92 Plastic-Encapsulate Transistors

D965R011 NPN Transistors



Features

- Audio Amplifier
- Flash Unit of Camera
- Switching Circuit

Marking: D965R011

Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	42	V
V_{CEO}	Collector Emitter Voltage	22	V
V_{EBO}	Emitter Base Voltage	6	V
I_C	Collector Current	5	A
P_C	Collector Power Dissipation	750	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C = 100μA, I_E = 0	42			V
$V_{(BR)CEO}$*	Collector-emitter breakdown voltage	I_C = 1mA, I_B = 0	22			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E = 10μA, I_C = 0	6			V
I_{CBO}	Collector cut-off current	V_{CB} = 30V, I_E = 0			100	nA
I_{EBO}	Emitter cut-off current	V_{EB} = 6V, I_C = 0			100	nA
$h_{FE(1)}$	DC current gain	V_{CE} = 5V, I_C = 1mA	150			
$h_{FE(2)}$		V_{CE} = 2V, I_C = 0.15mA	150			
$h_{FE(3)}$		V_{CE} = 2V, I_C = 500mA	600		1500	
$h_{FE(4)}$		V_{CE} = 2V, I_C = 2A	150			
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C = 3000mA, I_B = 100mA			0.35	V
f_T	Transition frequency	V_{CE}=6V, I_C=50mA, f=30MHz		150		MHz

Typical Characteristics